

**Trans IGBT Chip N-CH 600V 60A 260mW 3-Pin(2+Tab)  
D2PAK T/R**



Images are for reference only

**Manufacturer:** [STMicroelectronics, Inc](#)

**Package/Case:** TO-263

**Product Type:** Thyristors

**Lifecycle:** Active

[Inquiry](#)

## General Description

These devices are IGBTs developed using an advanced proprietary trench gate field-stop structure. These devices are part of the new HB series of IGBTs, which represent an optimum compromise between conduction and switching loss to maximize the efficiency of any frequency converter. Furthermore, the slightly positive VCE(sat) temperature coefficient and very tight parameter distribution result in safer paralleling operation.

## Key Features

Maximum junction temperature:  $T_J = 175\text{ }^\circ\text{C}$

High speed switching series

Minimized tail current

Low saturation voltage:  $V_{CE(sat)} = 1.55\text{ V (typ.) @ } I_C = 30\text{ A}$

Tight parameter distribution

Safe paralleling

Positive VCE(sat) temperature coefficient

Low thermal resistance

Very fast soft recovery antiparallel diode

## Recommended For You

### STGIF5CH60TS-L

STMicroelectronics, Inc

SDIP2B-26

### STGIPS10K60A

STMicroelectronics, Inc

SDIP-25L

### STP24NF10

STMicroelectronics, Inc

TO-220

**STGW30NC120HD**

STMicroelectronics, Inc

TO-247

**STGIPS20K60**

STMicroelectronics, Inc

SDIP-25

**STB75NF75LT4**

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TO-263

**STD20NF06LT4**

STMicroelectronics, Inc

TO-252

**STGW45HF60WD**

STMicroelectronics, Inc

TO-247

**STGW19NC60HD**

STMicroelectronics, Inc

TO-247

**STGW30NC60WD**

STMicroelectronics, Inc

TO-247

**STGW40H120DF2**

STMicroelectronics, Inc

TO-247

**STGW40V60DF**

STMicroelectronics, Inc

TO-247

**STGB10NC60HD**

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D2PAK

**STGB30V60DF**

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**STGP30H60DF**

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TO-220